

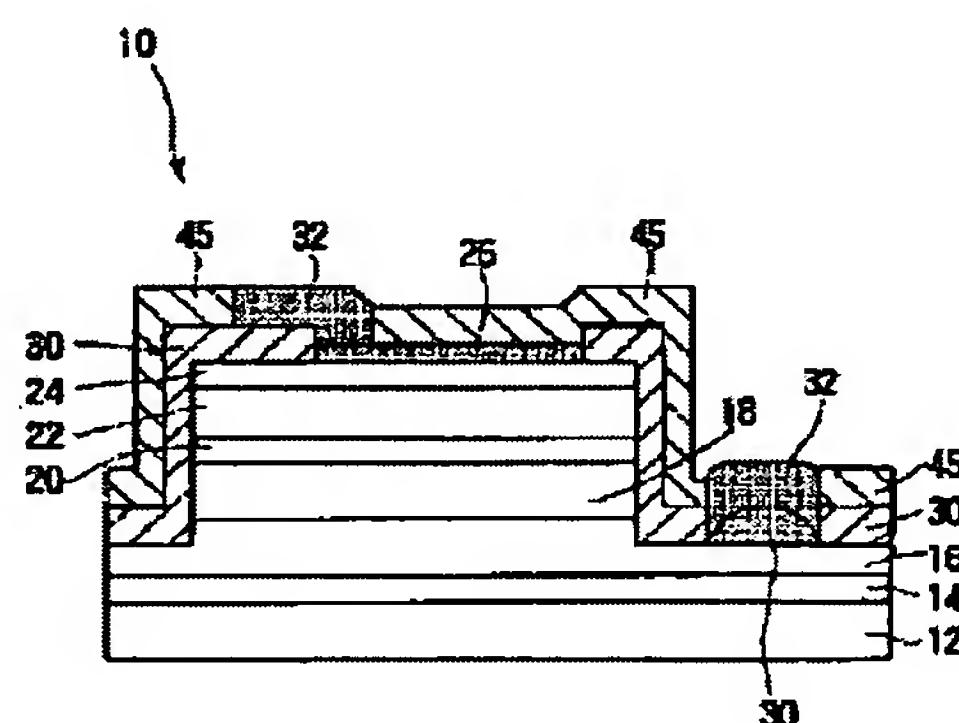
# **SEMICONDUCTOR LIGHT EMITTING ELEMENT, SEMICONDUCTOR LIGHT EMITTING DEVICE AND MANUFACTURE THEREOF**

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**Applicant:** TOKYO SHIBAURA ELECTRIC CO  
**Classification:**  
- **international:** H01L33/00; H01L33/00; (IPC1-7): H01L33/00; H01S3/18  
- **european:**  
**Application number:** JP19970237492 19970902  
**Priority number(s):** JP19970237492 19970902

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### Abstract of JP11087778

**PROBLEM TO BE SOLVED:** To make a light emission wavelength stable and allow light emission with high brightness in a wavelength in a region from visible light to infrared rays. **SOLUTION:** A fluorescent substance is included or deposited in any part of the semiconductor light emitting element 10. The fluorescent substance has an absorption peak in a wavelength band of 340 to 380 nm. Therefore, in order to effectively convert wavelength by the fluorescent substance, a light emitting layer 20 desirably emits ultraviolet rays of a wavelength band of 308 nm or less. A site to include the fluorescent substance in the semiconductor element 10 may be a p-side electrode layer 26, first. Then, a silicon oxide layer 45 or a current preventing layer 30 may follow. Alternatively any of respective semiconductor layers 14 to 24 may follow. A substrate 12 may follow further.



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